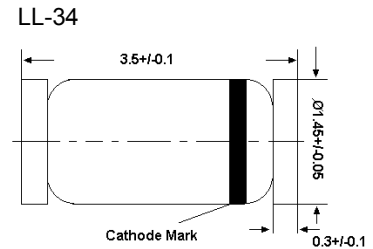


Silicon Epitaxial Planar Switching Diode

Fast switching diode in MiniMELF case especially suited for automatic surface mounting



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
at $t = 1\text{ s}$		1	
at $t = 1\text{ ms}$		4	
at $t = 1\text{ }\mu\text{s}$			
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$
¹⁾ Valid provided that electrodes are kept at ambient temperature.			

LL4148

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 10 mA	V _F	-	1	V
Leakage Current at V _R = 20 V at V _R = 75 V at V _R = 20 V, T _j = 150 °C	I _R I _R I _R	- - -	25 5 50	nA μA μA
Reverse Breakdown Voltage tested with 100 μA Pulses	V _{(BR)R}	100	-	V
Capacitance at V _R = 0, f = 1 MHz	C _{tot}	-	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses tp = 0.1 s, Rise Time < 30 ns, fp = 5 to 100 KHz	V _{fr}	-	2.5	V
Reverse Recovery Time at I _F = 10 mA to I _R = 1 mA, V _R = 6 V, R _L = 100 Ω	t _{rr}	-	4	ns
Thermal Resistance Junction to Ambient Air	R _{thA}	-	0.35 ¹⁾	K/mW
Rectification Efficiency at f = 100 MHz, V _{RF} = 2 V	η _v	0.45	-	-

¹⁾ Valid provided that electrodes are kept at ambient temperature.

